





LOW V_{CE(SAT)} PNP SURFACE MOUNT TRANSISTOR

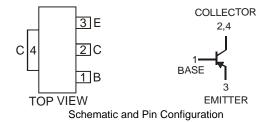
Features

- **Epitaxial Planar Die Construction**
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

SOT-223

Mechanical Data

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4 Ordering Information: See Page 4
- Weight: 0.115 grams (approximate)



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-180	V
Collector-Emitter Voltage	V _{CEO}	-140	V
Emitter-Base Voltage	V _{EBO}	-6	V
Continuous Collector Current	Ic	-4	Α
Peak Pulse Current	I _{CM}	-10	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T _A = 25°C	P _D	1	W
Thermal Resistance, Junction to Ambient Air (Note 3) @ T _A = 25°C	$R_{\theta JA}$	125	°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	°C

Notes:

- No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.



Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-180	_		V	$I_C = -100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-140	_		V	$I_{C} = -10 \text{mA}, I_{B} = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-6	_	_	V	$I_E = -100 \mu A, I_C = 0$
Collector Cutoff Current	I _{CBO}	_	_	-50 -1	nA μA	$V_{CB} = -150V, I_{E} = 0$ $V_{CB} = -150V, I_{E} = 0,$ $T_{A} = 100^{\circ}C$
Emitter Cutoff Current	I _{EBO}	_	_	-10	nA	$V_{EB} = -6V, I_{C} = 0$
ON CHARACTERISTICS (Note 4)						
Collector-Emitter Saturation Voltage	$V_{\text{CE(SAT)}}$		_ _ _	-60 -120 -150 -370	mV	$I_C = -100$ mA, $I_B = -5$ mA $I_C = -500$ mA, $I_B = -50$ mA $I_C = -1$ A, $I_B = -100$ mA $I_C = -3$ A, $I_B = -300$ mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_	_	-1110	mV	$I_C = -3A$, $I_B = -300mA$
Base-Emitter Turn-On Voltage	V _{BE(ON)}	_	_	-950	mV	$I_{C} = -3A, V_{CE} = -5V$
DC Current Gain	h _{FE}	100 100 75 —		300 — —	_	$\begin{split} I_C &= -10 \text{mA}, \ V_{CE} = -5 \text{V} \\ I_C &= -1 \text{A}, \ V_{CE} = -5 \text{V} \\ I_C &= -3 \text{A}, \ V_{CE} = -5 \text{V} \\ I_C &= -10 \text{A}, \ V_{CE} = -5 \text{V} \end{split}$
SMALL SIGNAL CHARACTERISTICS						
Current Gain-Bandwidth Product	f _T	_	150	_	MHz	$I_C = -100 \text{mA}, V_{CE} = -10 \text{V},$ f = 100 MHz
Output Capacitance	C _{obo}		40		pF	$V_{CB} = -20V$, $f = 1MHz$
SWITCHING CHARACTERISTICS						
Switching Times	t _{on} t _{off}		85 430		ns	$I_C = -1A$, $I_{B1} = -100mA$ $I_{B2} = 100mA$, $V_{CC} = -50V$

Notes: 4. Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤2%.

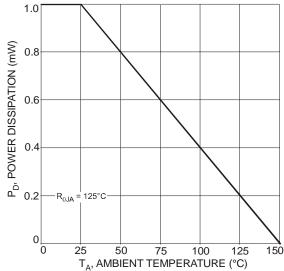


Fig. 1 Max Power Dissipation vs. Ambient Temperature

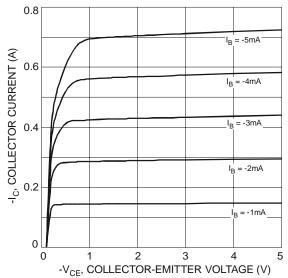
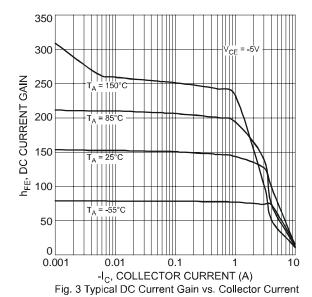
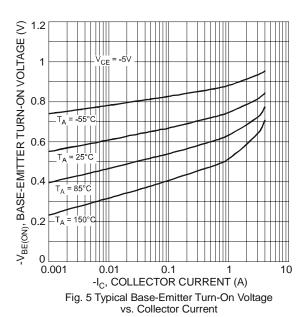
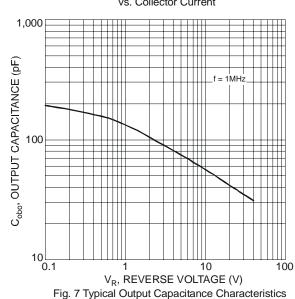


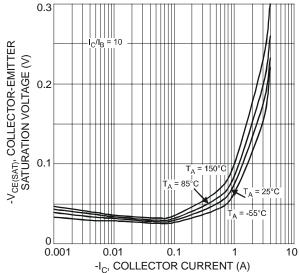
Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage











-I_C, COLLECTOR CURRENT (A)
Fig. 4 Typical Collector-Emitter Saturation Voltage
vs. Collector Current

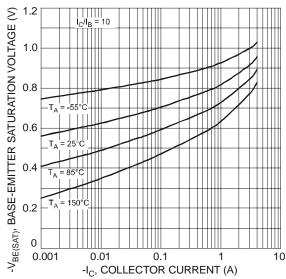


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

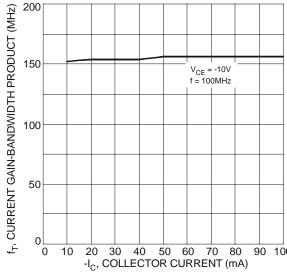


Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

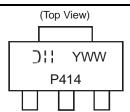


Ordering Information (Note 5)

Device	Packaging	Shipping
DZT955-13	SOT-223	2500/Tape & Reel

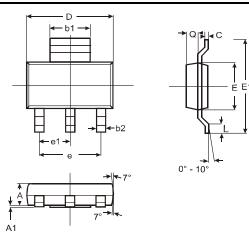
Notes: 5. For packaging details, go to our website at http://www.diodes.com/ap02007.pdf.

Marking Information



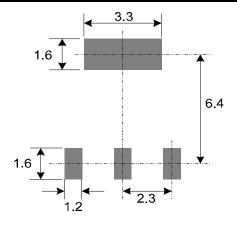
P414 = Product Type Marking Code YWW = Date Code Marking Y = Last digit of year ex: 7 = 2007 WW = Week code 01 - 52

Package Outline Dimensions



SOT-223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b1	2.90	3.10	3.00		
b2	0.60	0.80	0.70		
C	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	_	_	4.60		
e1			2.30		
L	0.85	1.05	0.95		
q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout: (Dimensions in mm)



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>>Diodes Incorporated(达迩科技(美台))